

2N5679 2N5680 PNP  
2N5681 2N5682 NPN

**COMPLEMENTARY  
SILICON POWER TRANSISTORS**



**TO-39 CASE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N5679, 2N5681 series devices are complementary silicon power transistors, manufactured by the epitaxial planar process, designed for general purpose amplifier and switching applications where high voltages are required.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

	SYMBOL	2N5679 2N5681	2N5680 2N5682	UNITS
Collector-Base Voltage	$V_{CBO}$	100	120	V
Collector-Emitter Voltage	$V_{CEO}$	100	120	V
Emitter-Base Voltage	$V_{EBO}$		4.0	V
Continuous Collector Current	$I_C$		1.0	A
Continuous Base Current	$I_B$		0.5	A
Power Dissipation	$P_D$		1.0	W
Power Dissipation ( $T_C=25^\circ\text{C}$ )	$P_D$		10	W
Operating and Storage Junction Temperature	$T_J, T_{stg}$		-65 to +200	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$		175	$^\circ\text{C/W}$
Thermal Resistance	$\theta_{JC}$		17.5	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=\text{Rated } V_{CBO}$		1.0	$\mu\text{A}$
$I_{CEV}$	$V_{CE}=\text{Rated } V_{CEO}, V_{EB}=1.5\text{V}$		1.0	$\mu\text{A}$
$I_{CEV}$	$V_{CE}=\text{Rated } V_{CEO}, V_{EB}=1.5\text{V}, T_C=150^\circ\text{C}$		1.0	mA
$I_{CEO}$	$V_{CE}=70\text{V}$ (2N5679, 2N5681)		10	$\mu\text{A}$
$I_{CEO}$	$V_{CE}=80\text{V}$ (2N5680, 2N5682)		10	$\mu\text{A}$
$I_{EBO}$	$V_{EB}=4.0\text{V}$		1.0	$\mu\text{A}$
$BV_{CEO}$	$I_C=10\text{mA}$ (2N5679, 2N5681)	100		V
$BV_{CEO}$	$I_C=10\text{mA}$ (2N5680, 2N5682)	120		V
$V_{CE(SAT)}$	$I_C=250\text{mA}, I_B=25\text{mA}$		0.6	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.0	V
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=200\text{mA}$		2.0	V
$V_{BE(ON)}$	$V_{CE}=2.0\text{V}, I_C=250\text{mA}$		1.0	V
$h_{FE}$	$V_{CE}=2.0\text{V}, I_C=250\text{mA}$	40	150	
$h_{FE}$	$V_{CE}=2.0\text{V}, I_C=1.0\text{A}$	5.0		
$h_{fe}$	$V_{CE}=1.5\text{V}, I_C=0.2\text{A}, f=1.0\text{kHz}$	40		
$f_T$	$V_{CE}=10\text{V}, I_C=100\text{mA}, f=10\text{MHz}$	30		MHz
$C_{ob}$	$V_{CB}=20\text{V}, I_E=0, f=1.0\text{MHz}$		50	pF

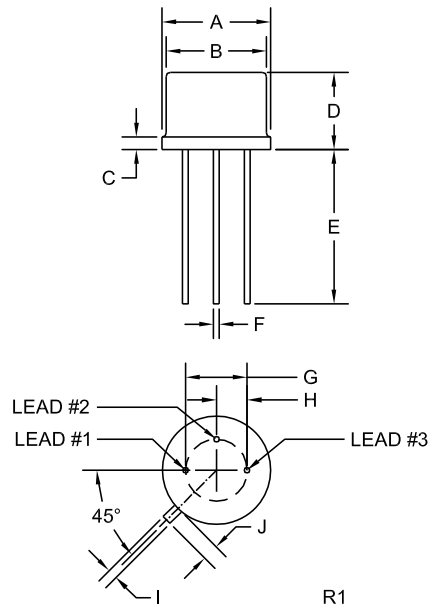
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TO-39 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

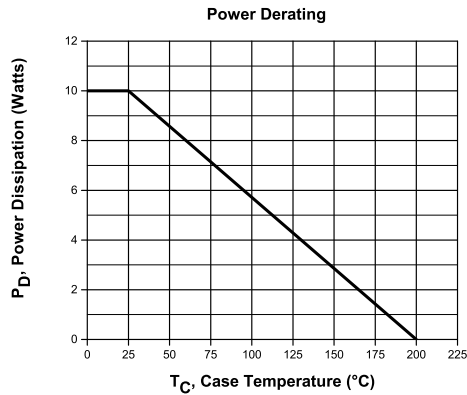
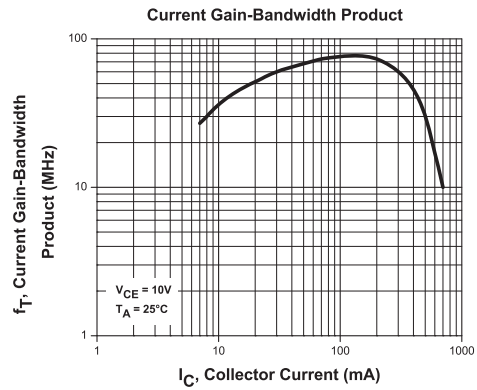
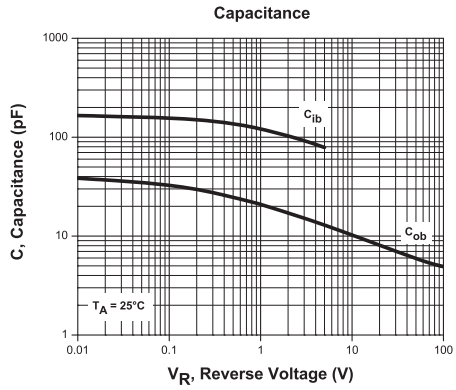
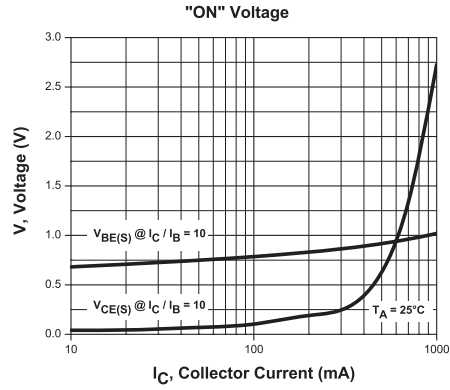
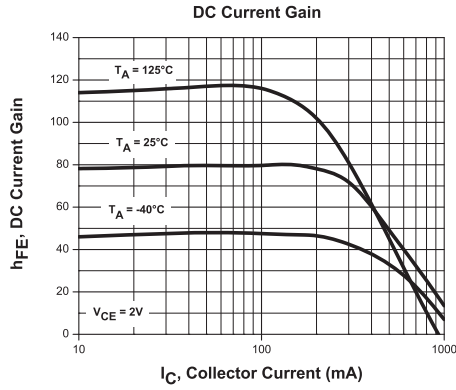
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PNP TYPICAL ELECTRICAL CHARACTERISTICS



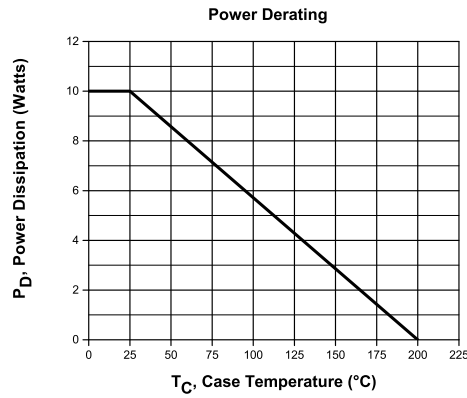
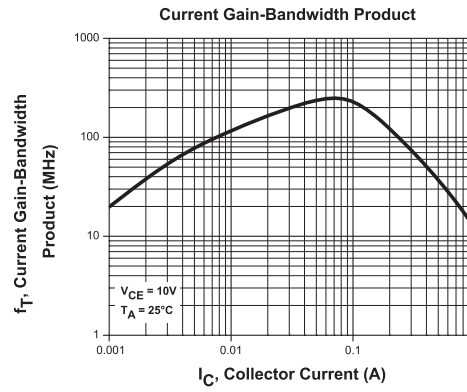
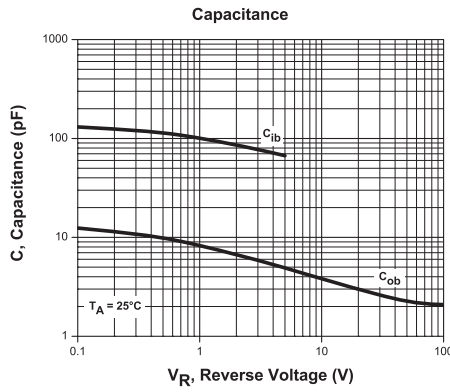
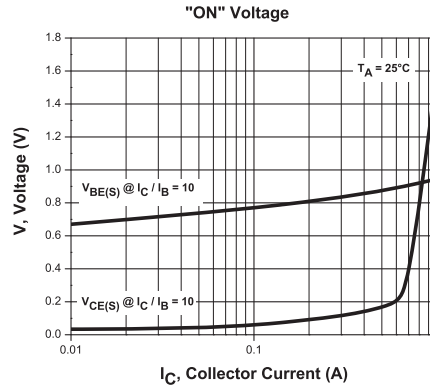
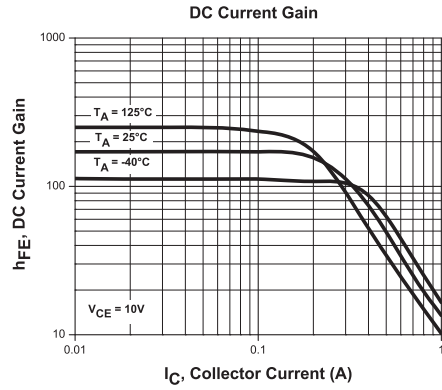
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**NPN TYPICAL ELECTRICAL CHARACTERISTICS**



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